

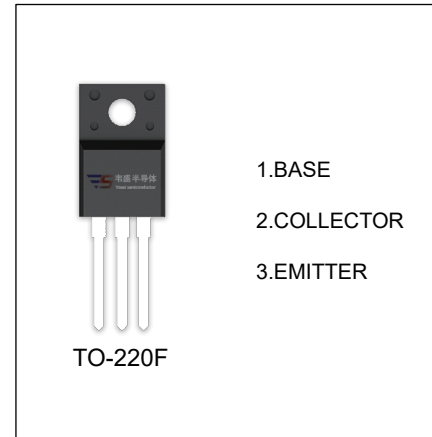
2SD2061 TRANSISTOR (NPN)

FEATURES

- Low Saturation Voltage
- Excellent DC Current Gain Characteristic

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	80	V
V _{CEO}	Collector-Emitter Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	3	A
P _C	Collector Power Dissipation	2	W
T _J , T _{STG}	Operation Junction and Storage Temperature Range	-55-150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =50μA, I _E =0	80			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	60			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =50μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =60V, I _E =0			10	μA
Emitter cut-off current	I _{EBO}	V _{EB} =4V, I _C =0			10	μA
DC current gain	h _{FE}	V _{CE} =5V, I _C =0.5A	100		320	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =2A, I _B =0.2A			1	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =2A, I _B =0.2A			1.5	V
Transition frequency	f _T	V _{CE} =5V, I _C =0.5A, f=5MHz		8		MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		70		pF

